

Abstract of the Disclosure:

A semiconductor element has a semiconductor body of a first conductivity type. The semiconductor body has a zone of a second conductivity type embedded. Further regions of the 5 second conductivity type surround the zone of the second conductivity type like a well. The further regions are interrupted in at least one location by a channel that is formed by the semiconductor body. The further regions are doped with a doping concentration that is high enough so that 10 the further regions are not completely depleted of charge carriers when the semiconductor element is reverse-biased.

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